

## isc N-Channel MOSFET Transistor

**IRFI4110G,IIRFI4110G**

### • FEATURES

- Low drain-source on-resistance:  
 $R_{DS(on)} \leq 4.5\text{m}\Omega$  (max)
- Enhancement mode
- Fast Switching Speed
- 100% avalanche tested
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

### • DESCRIPTION

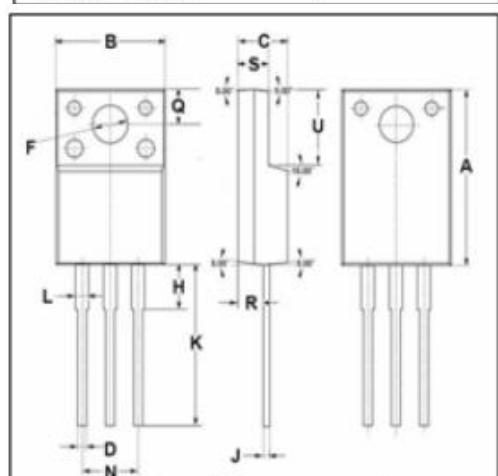
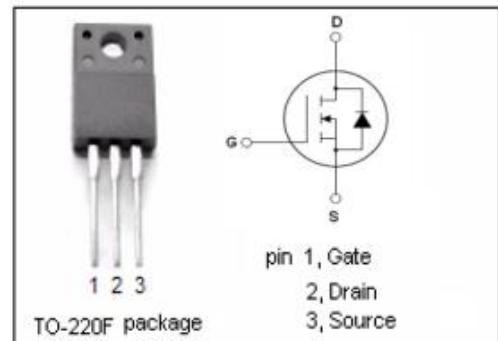
- High speed power switching
- Hard switch and high frequency circuits

### • ABSOLUTE MAXIMUM RATINGS( $T_a=25^\circ\text{C}$ )

| SYMBOL    | PARAMETER                                  | VALUE    | UNIT             |
|-----------|--|----------|------------------|
| $V_{DSS}$ | Drain-Source Voltage                       | 100      | V                |
| $V_{GS}$  | Gate-Source Voltage                        | $\pm 20$ | V                |
| $I_D$     | Drain Current-Continuous                   | 72       | A                |
| $I_{DM}$  | Drain Current-Single Pulsed                | 290      | A                |
| $P_D$     | Total Dissipation @ $T_c=25^\circ\text{C}$ | 61       | W                |
| $T_j$     | Max. Operating Junction Temperature        | 175      | $^\circ\text{C}$ |
| $T_{stg}$ | Storage Temperature                        | -55~175  | $^\circ\text{C}$ |

### • THERMAL CHARACTERISTICS

| SYMBOL         | PARAMETER                          | MAX  | UNIT                      |
|----------------|------------------------------------|------|---------------------------|
| $R_{th(ch-c)}$ | Channel-to-case thermal resistance | 2.46 | $^\circ\text{C}/\text{W}$ |



| DIM | mm    |       |
|-----|-------|-------|
|     | MIN   | MAX   |
| A   | 14.95 | 15.05 |
| B   | 10.00 | 10.10 |
| C   | 4.40  | 4.60  |
| D   | 0.75  | 0.90  |
| F   | 3.10  | 3.30  |
| H   | 3.70  | 3.90  |
| J   | 0.50  | 0.70  |
| K   | 13.4  | 13.6  |
| L   | 1.10  | 1.30  |
| N   | 5.00  | 5.20  |
| Q   | 2.70  | 2.90  |
| R   | 2.20  | 2.40  |
| S   | 2.65  | 2.90  |
| U   | 6.40  | 6.60  |

**isc N-Channel MOSFET Transistor****IRFI4110G,IIRFI4110G****ELECTRICAL CHARACTERISTICS****T<sub>c</sub>=25°C unless otherwise specified**

| SYMBOL              | PARAMETER                      | CONDITIONS   | MIN | TYP | MAX  | UNIT |
|---------------------|--------------------------------|--|-----|-----|------|------|
| BV <sub>DSS</sub>   | Drain-Source Breakdown Voltage | V <sub>GS</sub> =0V; I <sub>D</sub> =0.25mA                | 100 |     |      | V    |
| V <sub>GS(th)</sub> | Gate Threshold Voltage         | V <sub>DS</sub> = V <sub>GS</sub> ; I <sub>D</sub> =0.25mA | 2.0 |     | 4.0  | V    |
| R <sub>DS(on)</sub> | Drain-Source On-Resistance     | V <sub>GS</sub> =10V; I <sub>D</sub> =43A                  |     |     | 4.5  | mΩ   |
| I <sub>GSS</sub>    | Gate-Source Leakage Current    | V <sub>GS</sub> = ±20V; V <sub>DS</sub> = 0V               |     |     | ±100 | nA   |
| I <sub>DSS</sub>    | Drain-Source Leakage Current   | V <sub>DS</sub> =100V; V <sub>GS</sub> = 0V                |     |     | 20   | μ A  |
| V <sub>SD</sub>     | Diode forward voltage          | I <sub>DR</sub> =43, V <sub>GS</sub> = 0 V                 |     |     | 1.3  | V    |

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